

74ALVC541

Octal buffer/line driver; 3-state

Rev. 02 — 5 November 2007

Product data sheet

1. General description

The 74ALVC541 is an octal non-inverting buffer/line drivers with 3-state bus compatible outputs. The 3-state outputs are controlled by the output enable inputs $\overline{OE}0$ and $\overline{OE}1$. A HIGH on $\overline{OE}n$ causes the outputs to assume a high-impedance OFF-state.

2. Features

- Wide supply voltage range from 1.65 V to 3.6 V
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.5 V)
 - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- 3.6 V tolerant inputs/outputs
- CMOS low power consumption
- Direct interface with TTL levels (2.7 V to 3.6 V)
- Power-down mode
- Latch-up performance exceeds 250 mA
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74ALVC541D	-40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74ALVC541PW	-40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74ALVC541BQ	-40 °C to +85 °C	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1

4. Functional diagram

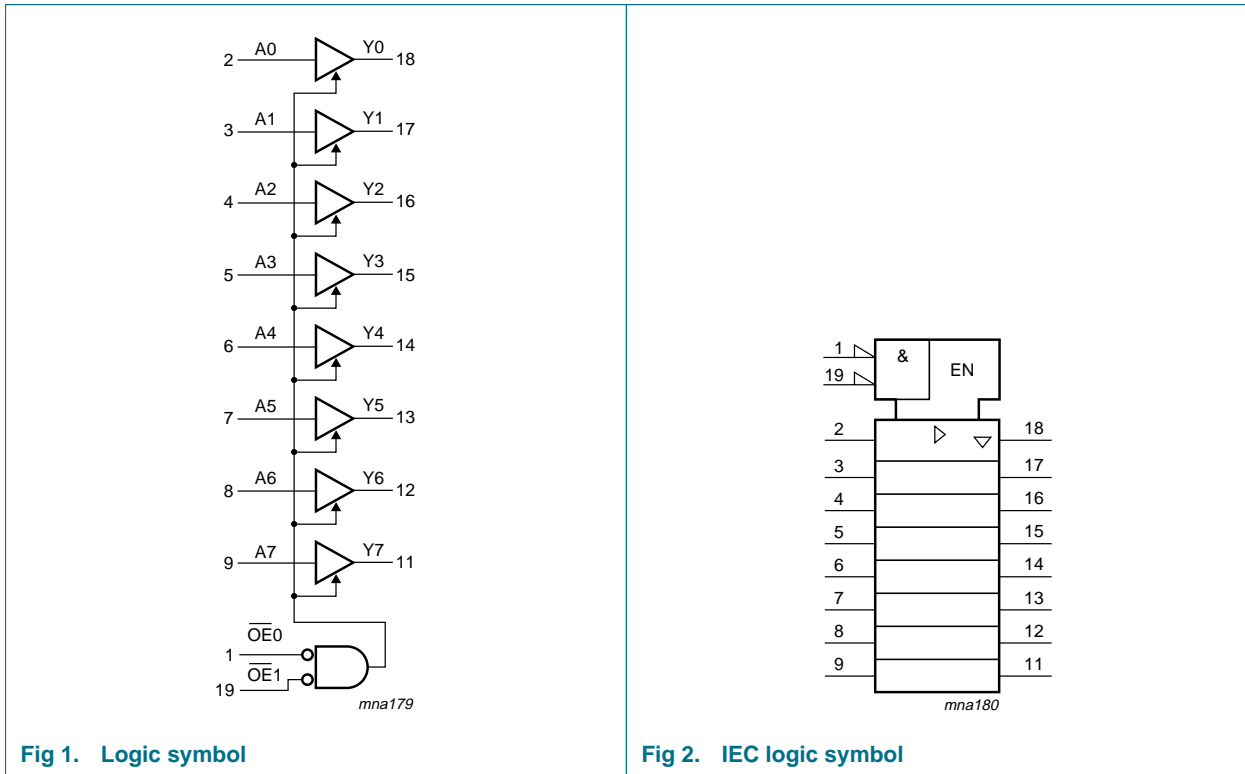
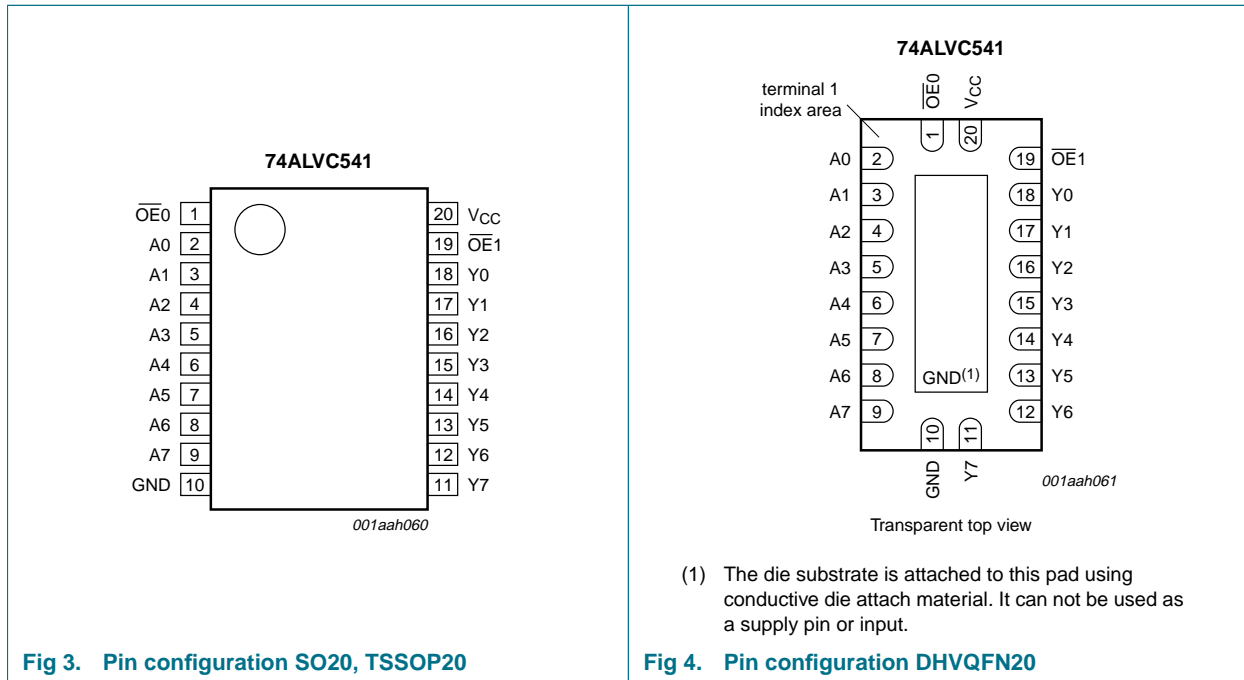


Fig 1. Logic symbol

Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{OE}0$	1	output enable input (active LOW)
A[0:7]	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
Y[0:7]	18, 17, 16, 15, 14, 13, 12, 11	data output
$\overline{OE}1$	19	output enable input (active LOW)
V _{CC}	20	supply voltage

6. Functional description

Table 3. Functional table^[1]

Control		Input		Output
$\overline{OE}0$	$\overline{OE}1$	An		Yn
L	L	L		L
L	L	H		H
X	H	X		Z
H	X	X		Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
V_I	input voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	^[1] -50	-	mA
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	± 50	mA
V_O	output voltage	output HIGH or LOW state	^[2] -0.5	$V_{CC} + 0.5$	V
		output 3-state	^[2] -0.5	+4.6	V
		power-down mode, $V_{CC} = 0$ V	^[3] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	± 50	mA
I_{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +85 °C			
	SO20 package		^[4] -	500	mW
	TSSOP20 package		^[5] -	500	mW
	DHVQFN20 package		^[6] -	500	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 3.6 V in normal operation.

[4] P_{tot} derates linearly with 8 mW/K above 70 °C.

[5] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[6] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	output HIGH or LOW state	0	V_{CC}	V
		output 3-state	0	3.6	V
		power-down mode, $V_{CC} = 0$ V	0	3.6	V
T_{amb}	ambient temperature		-40	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65$ V to 2.7 V	-	20	ns/V
		$V_{CC} = 2.7$ V to 3.6 V	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7$ V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7$ V to 3.6 V	-	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100$ μ A; $V_{CC} = 1.65$ V to 3.6 V	$V_{CC} - 0.2$	-	-	V
		$I_O = 6$ mA; $V_{CC} = 1.65$ V	1.25	-	-	V
		$I_O = 12$ mA; $V_{CC} = 2.3$ V	1.8	-	-	V
		$I_O = 18$ mA; $V_{CC} = 2.3$ V	1.7	-	-	V
		$I_O = 12$ mA; $V_{CC} = 2.7$ V	2.2	-	-	V
		$I_O = 18$ mA; $V_{CC} = 3.0$ V	2.4	-	-	V
		$I_O = 24$ mA; $V_{CC} = 3.0$ V	2.2	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100$ μ A; $V_{CC} = 1.65$ V to 3.6 V	-	-	0.2	V
		$I_O = -6$ mA; $V_{CC} = 1.65$ V	-	-	0.3	V
		$I_O = -12$ mA; $V_{CC} = 2.3$ V	-	-	0.4	V
		$I_O = -18$ mA; $V_{CC} = 2.3$ V	-	-	0.6	V
		$I_O = -12$ mA; $V_{CC} = 2.7$ V	-	-	0.4	V
		$I_O = -18$ mA; $V_{CC} = 3.0$ V	-	-	0.4	V
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	-	-	0.55	V
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 3.6$ V	-	± 0.1	± 10.0	μ A

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 3.6$ V	-	± 0.1	± 5.0	μA
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	± 0.1	± 10.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 3.6$ V	-	0.2	10	μA
ΔI_{CC}	additional supply current	per input pin; $V_{CC} = 3.0$ V to 3.6 V; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A;	-	5	750	μA
C_I	input capacitance		-	3.5	-	pF

[1] All typical values are measured at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C.

10. Dynamic characteristics

Table 7. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

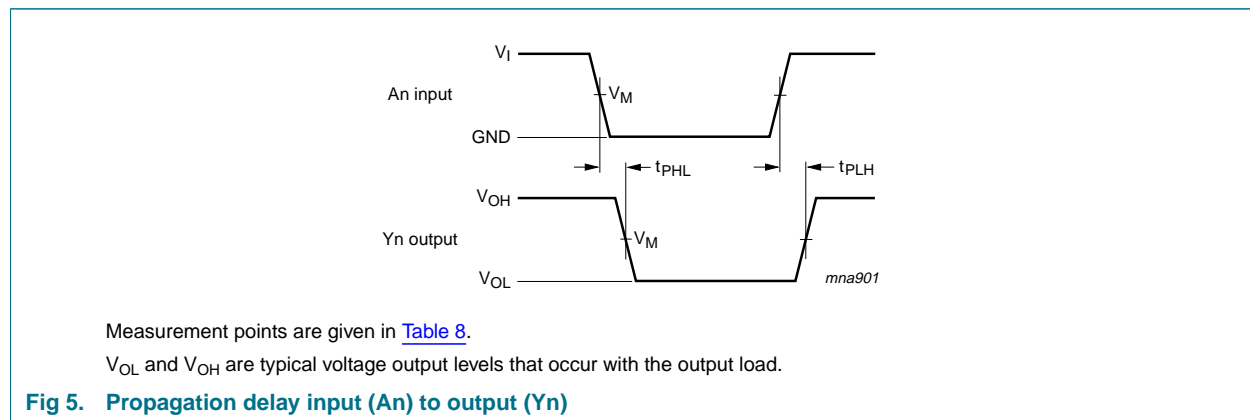
Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
t_{pd}	propagation delay	An to Yn; see Figure 5 ^[2]				
		$V_{CC} = 1.65$ V to 1.95 V	1.0	3.0	4.6	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.0	2.2	3.3	ns
		$V_{CC} = 2.7$ V	1.0	2.5	3.3	ns
t_{en}	enable time	$\overline{O}En$ to Yn; see Figure 6 ^[2]				
		$V_{CC} = 1.65$ V to 1.95 V	1.0	4.2	7.5	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.0	3.3	5.4	ns
		$V_{CC} = 2.7$ V	1.0	3.7	5.8	ns
t_{dis}	disable time	$\overline{O}En$ to Yn; see Figure 6 ^[2]				
		$V_{CC} = 1.65$ V to 1.95 V	1.0	4.8	7.5	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.0	3.1	4.5	ns
		$V_{CC} = 2.7$ V	1.0	3.1	4.8	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.0	2.9	4.6	ns

Table 7. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC} ; V _{CC} = 3.3 V ^[3]				
		outputs enabled	-	25	-	pF
		outputs disabled	-	0	-	pF

- [1] All typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V and 3.3 V.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
 t_{en} is the same as t_{PZL} and t_{PZH}.
 t_{dis} is the same as t_{PLZ} and t_{PHZ}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

11. Waveforms



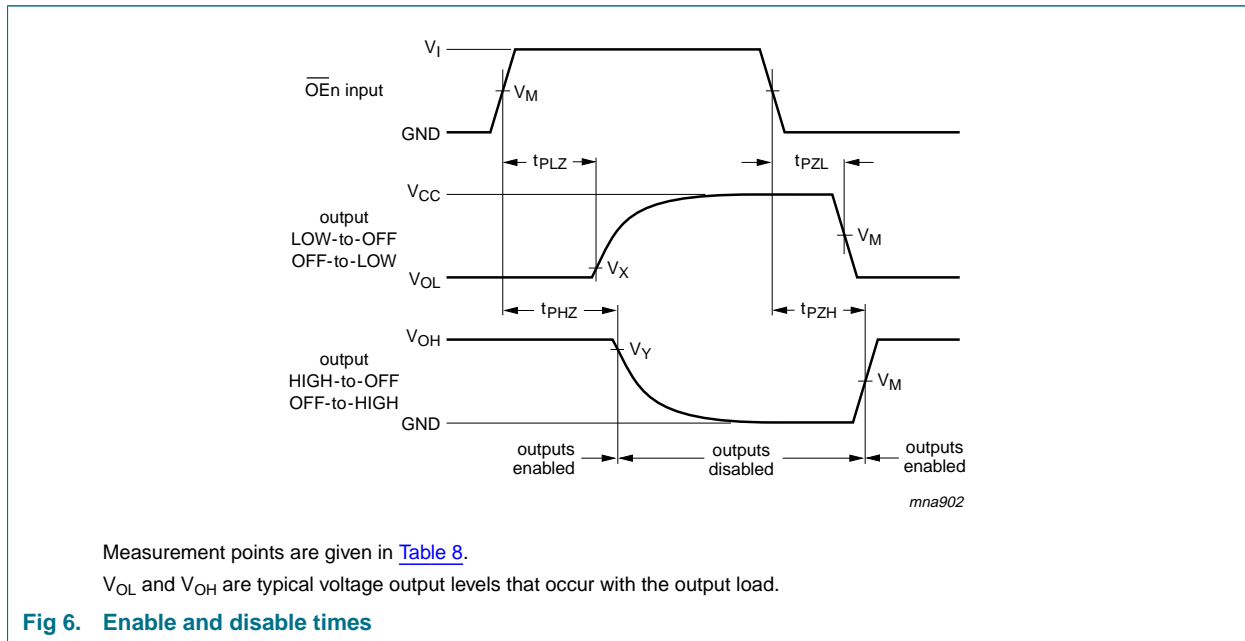


Table 8. Measurement points

Supply voltage	Input		Output		
	V_I	V_M	V_M	V_X	V_Y
1.65 V to 1.95 V	V_{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$
2.3 V to 2.7 V	V_{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$
2.7 V	2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$
3.0 V to 3.6 V	2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$

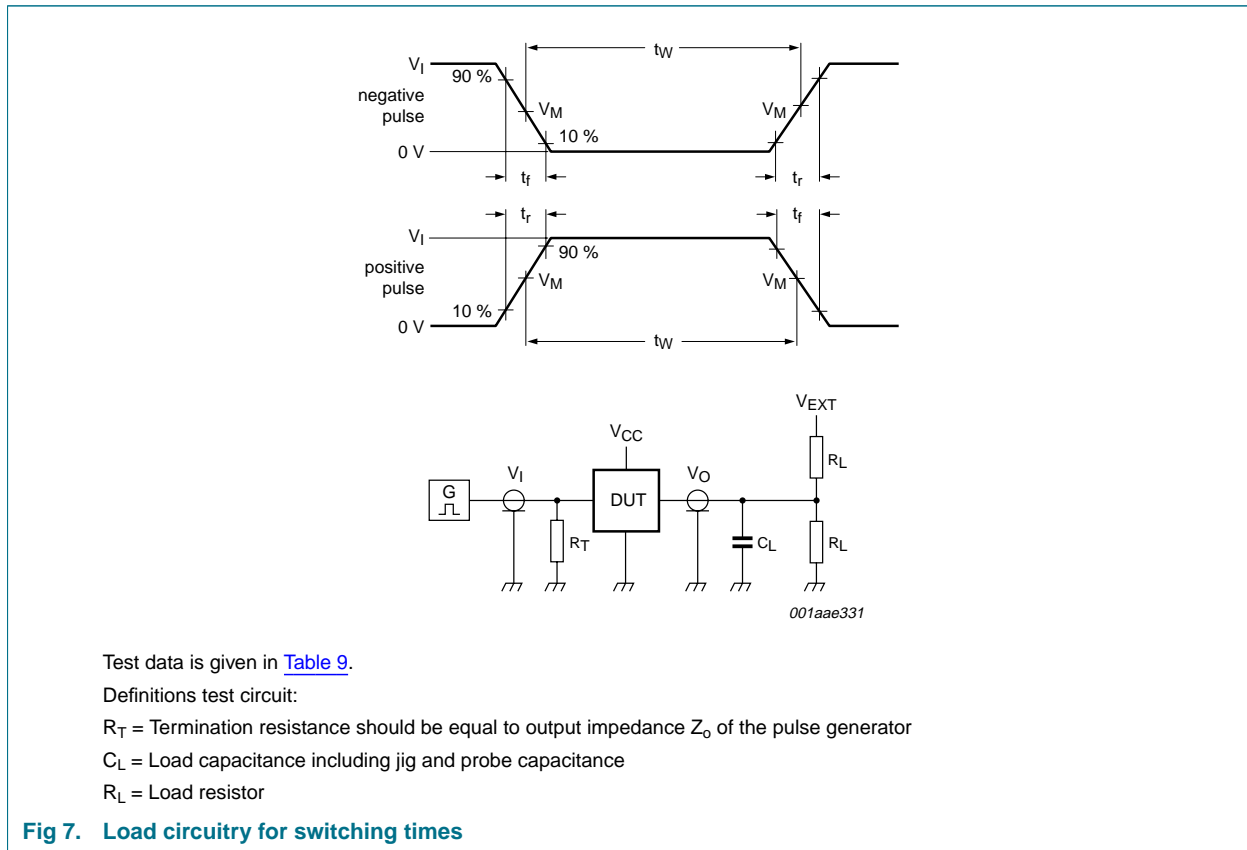


Table 9. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PLZ}, t_{PZL}	t_{PHZ}, t_{PZH}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open	$2 \times V_{CC}$	GND
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	$2 \times V_{CC}$	GND
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	6	GND
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	6	GND

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

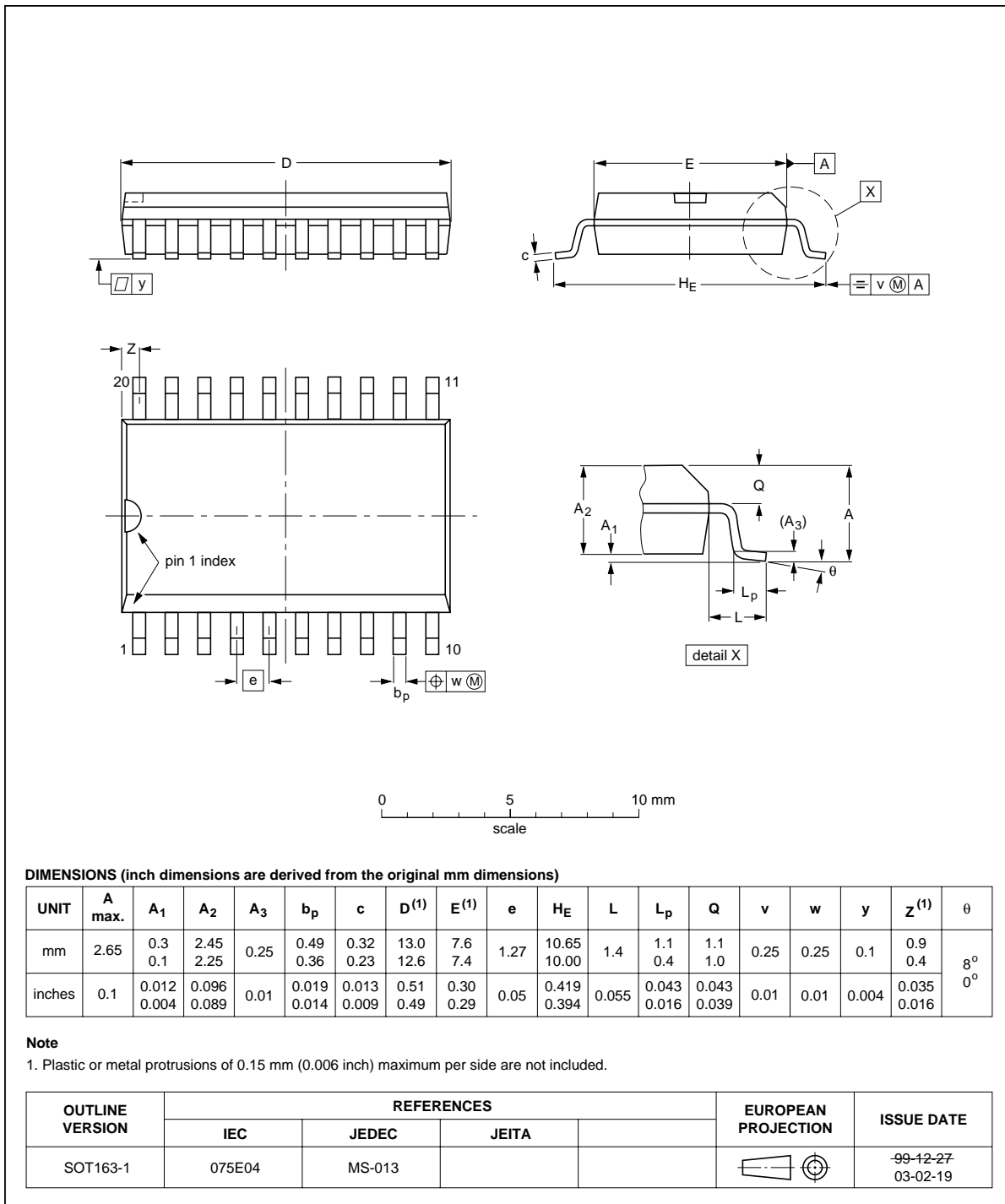


Fig 8. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

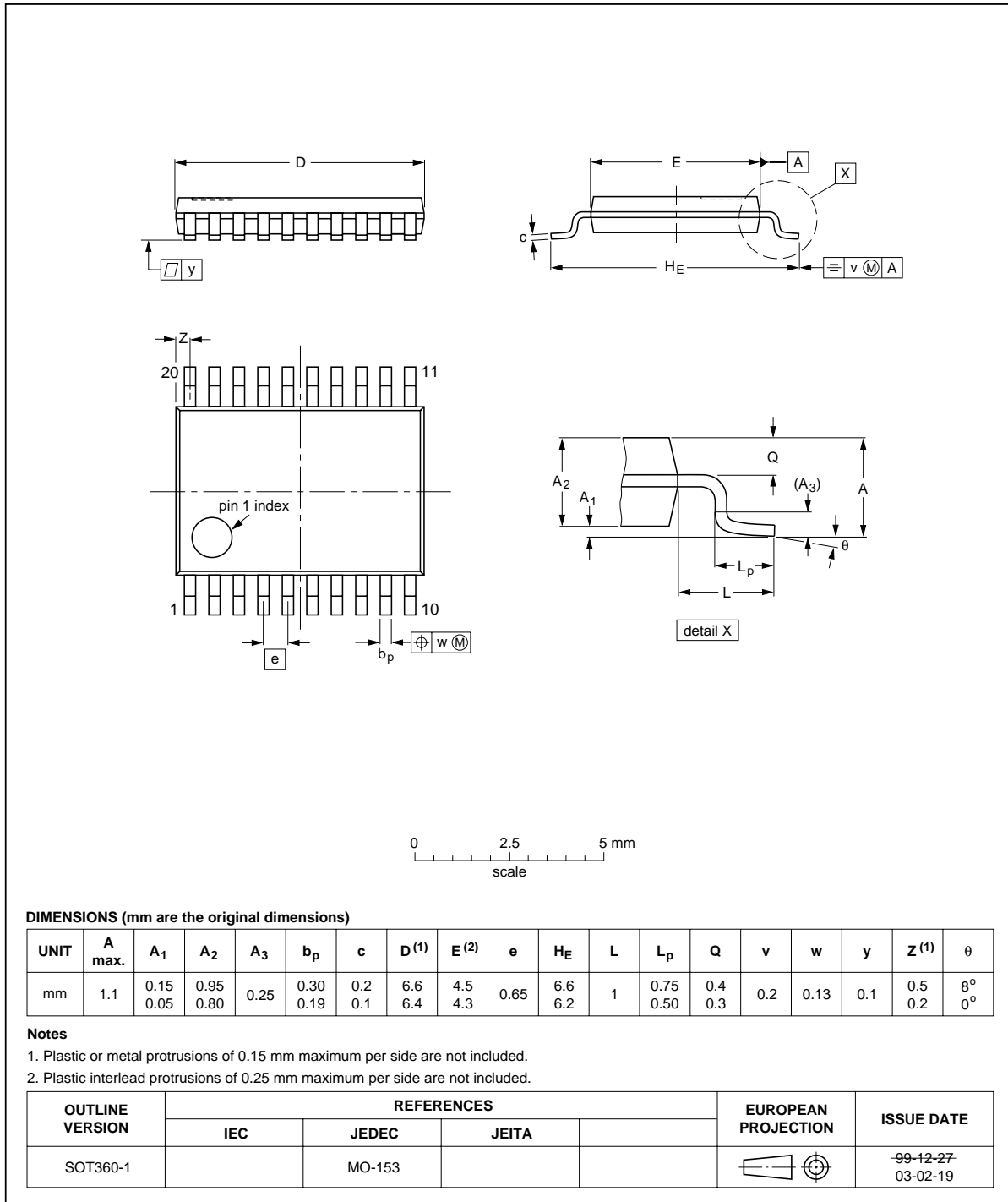


Fig 9. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

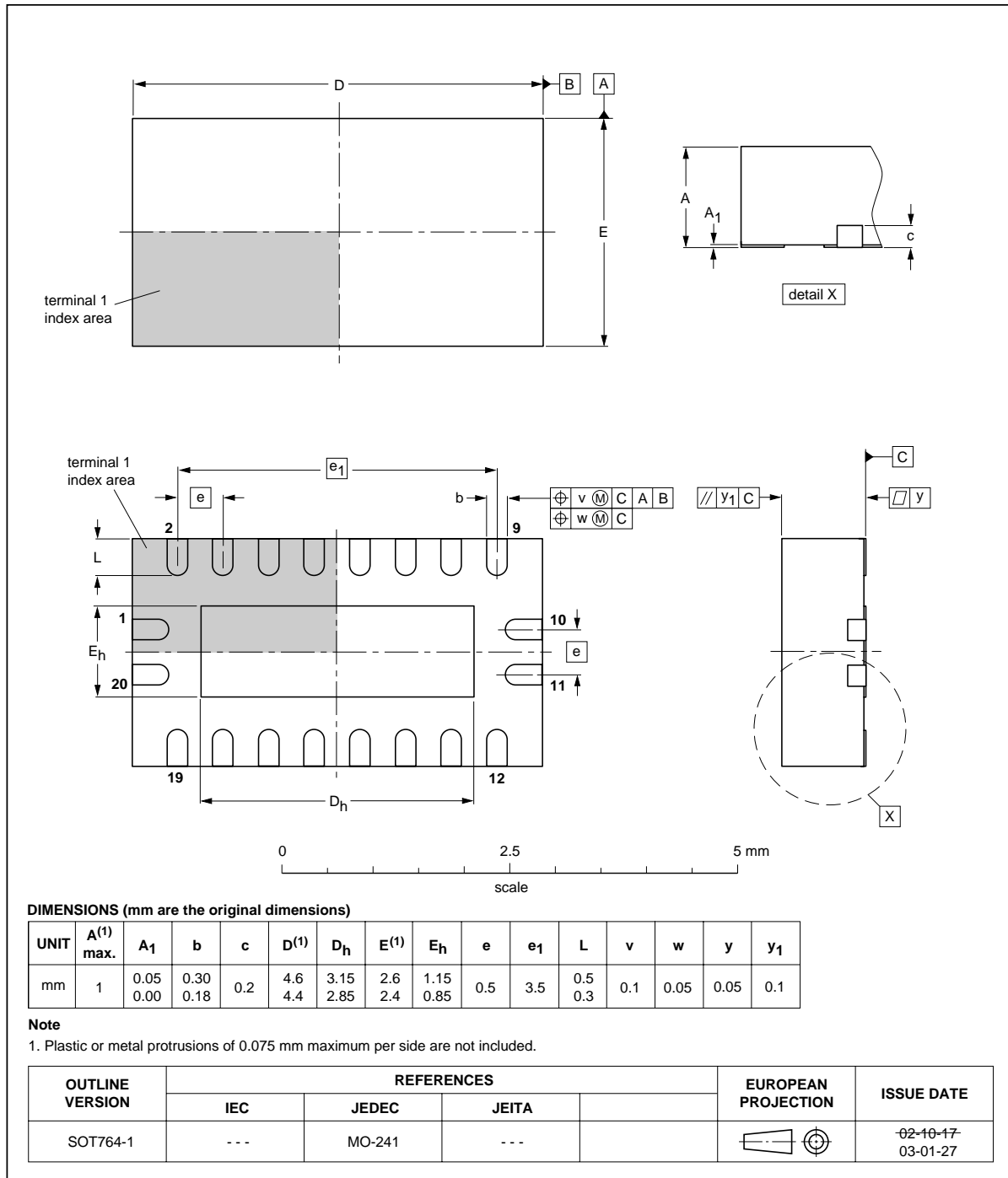


Fig 10. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged-Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74ALVC541_2	20071105	Product data sheet	-	74ALVC541_1
Modifications:	<ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3: DHVQFN20 package added. • Section 8: derating values added for DHVQFN20 package. • Section 12: outline drawing added for DHVQFN20 package. 			
74ALVC541_1	20020226	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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